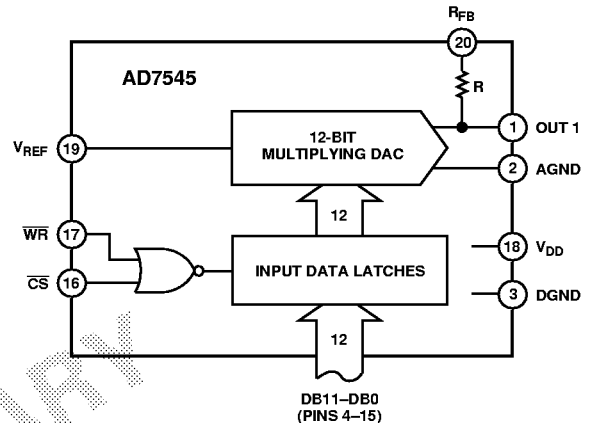


## AD7545

### FEATURES

- 12-Bit Resolution
- Low Gain TC: 2 ppm/°C typ
- Fast TTL Compatible Data Latches
- Single +5 V to +15 V Supply
- Small 20-Lead 0.3" DIP and 20-Terminal Surface Mount Packages
- Latch Free (Schottky Protection Diode Not Required)
- Low Cost
- Ideal for Battery Operated Equipment

### FUNCTIONAL BLOCK DIAGRAM



### GENERAL DESCRIPTION

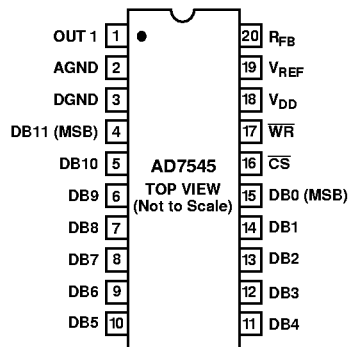
The AD7545 is a monolithic 12-bit CMOS multiplying DAC with onboard data latches. It is loaded by a single 12-bit wide word and directly interfaces to most 12- and 16-bit bus systems. Data is loaded into the input latches under the control of the CS and WR inputs; tying these control inputs low makes the input latches transparent, allowing direct unbuffered operation of the DAC.

The AD7545 is particularly suitable for single supply operation and applications with wide temperature variations.

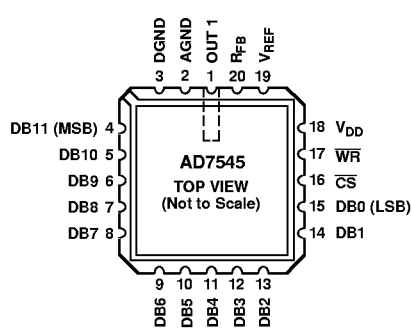
The AD7545 can be used with any supply voltage from +5 V to +15 V. With CMOS logic levels at the inputs the device dissipates less than 0.5 mW for  $V_{DD} = +5$  V.

### PIN CONFIGURATIONS

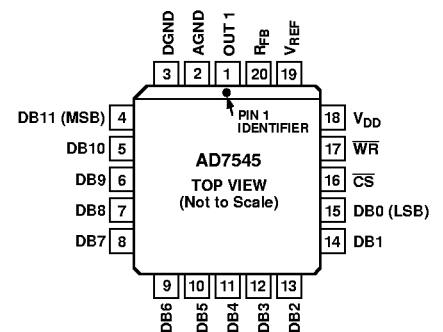
#### DIP



#### LCCC



#### PLCC



### REV. A

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# AD7545—SPECIFICATIONS ( $V_{REF} = +10\text{ V}$ , $V_{OUT1} = 0\text{ V}$ , $AGND = DGND$ unless otherwise noted)

Parameter	Version	$V_{DD} = +5\text{ V}$ Limits		$V_{DD} = +15\text{ V}$ Limits		Units	Test Conditions/Comments
		$T_A = +25^\circ\text{C}$	$T_{MIN}, T_{MAX}^1$	$T_A = +25^\circ\text{C}$	$T_{MIN}, T_{MAX}^1$		
<b>STATIC PERFORMANCE</b>							
Resolution	All	12	12	12	12	Bits	
	J, A, S	$\pm 2$	$\pm 2$	$\pm 2$	$\pm 2$	LSB max	
	K, B, T	$\pm 1$	$\pm 1$	$\pm 1$	$\pm 1$	LSB max	
	L, C, U	$\pm 1/2$	$\pm 1/2$	$\pm 1/2$	$\pm 1/2$	LSB max	
	GL, GC, GU	$\pm 1/2$	$\pm 1/2$	$\pm 1/2$	$\pm 1/2$	LSB max	
Differential Nonlinearity	J, A, S	$\pm 4$	$\pm 4$	$\pm 4$	$\pm 4$	LSB max	10-Bit Monotonic $T_{MIN}$ to $T_{MAX}$
	K, B, T	$\pm 1$	$\pm 1$	$\pm 1$	$\pm 1$	LSB max	12-Bit Monotonic $T_{MIN}$ to $T_{MAX}$
	L, C, U	$\pm 1$	$\pm 1$	$\pm 1$	$\pm 1$	LSB max	12-Bit Monotonic $T_{MIN}$ to $T_{MAX}$
	GL, GC, GU	$\pm 1$	$\pm 1$	$\pm 1$	$\pm 1$	LSB max	12-Bit Monotonic $T_{MIN}$ to $T_{MAX}$
Gain Error (Using Internal RFB) <sup>2</sup>	J, A, S	$\pm 20$	$\pm 20$	$\pm 25$	$\pm 25$	LSB max	DAC Register Loaded with 1111 1111 1111
	K, B, T	$\pm 10$	$\pm 10$	$\pm 15$	$\pm 15$	LSB max	Gain Error Is Adjustable Using the Circuits of Figures 4, 5, and 6
	L, C, U	$\pm 5$	$\pm 6$	$\pm 10$	$\pm 10$	LSB max	
	GL, GC, GU	$\pm 1$	$\pm 2$	$\pm 6$	$\pm 7$	LSB max	
Gain Temperature Coefficient <sup>3</sup>	All	$\pm 5$	$\pm 5$	$\pm 10$	$\pm 10$	ppm/°C max	Typical Value is 2 ppm/°C for $V_{DD} = +5\text{ V}$
$\Delta\text{Gain}/\Delta\text{Temperature}$	All	$\pm 5$	$\pm 5$	$\pm 10$	$\pm 10$	ppm/°C max	
DC Supply Rejection <sup>3</sup>	All	0.015	0.03	0.01	0.02	% per % max	$\Delta V_{DD} = \pm 5\%$
$\Delta\text{Gain}/\Delta V_{DD}$	All	0.015	0.03	0.01	0.02	% per % max	
Output Leakage Current at OUT1	J, K, L, GL	10	50	10	50	nA max	$DB0-DB11 = 0\text{ V}$ ; $\overline{WR}, \overline{CS} = 0\text{ V}$
	A, B, C, GC	10	50	10	50	nA max	
	S, T, U, GU	10	200	10	200	nA max	
<b>DYNAMIC PERFORMANCE</b>							
Current Settling Time <sup>3</sup>	All	2	2	2	2	$\mu\text{s}$ max	To 1/2 LSB. OUT1 Load = 100 $\Omega$ . DAC Output Measured from Falling Edge of $\overline{WR}, \overline{CS} = 0$ .
Propagation Delay <sup>3</sup> (from Digital Input Change to 90% of Final Analog Output)	All	300	—	250	—	ns max	OUT1 Load = 100 $\Omega$ , $C_{EXT} = 13\text{ pF}^4$
Digital-to-Analog Glitch Inpulse AC Feedthrough <sup>5</sup>	All	400	—	250	—	nV sec typ	$V_{REF} = AGND$
At OUT1	All	5	5	5	5	mV p-p typ	$V_{REF} = \pm 10\text{ V}$ , 10 kHz Sinewave
<b>REFERENCE INPUT</b>							
Input Resistance (Pin 19 to GND)	All	7 25	7 25	7 25	7 25	k $\Omega$ min k $\Omega$ max	Input Resistance TC = -300 ppm/°C typ Typical Input Resistance = 11 k $\Omega$
<b>ANALOG OUTPUT</b>							
Output Capacitance <sup>3</sup>	All	70	70	70	70	pF max	$DB0-DB11 = 0\text{ V}$ , $\overline{WR}, \overline{CS} = 0\text{ V}$
$C_{OUT1}$	All	70	70	70	70	pF max	$DB0-DB11 = V_{DD}$ , $\overline{WR}, \overline{CS} = 0\text{ V}$
$C_{OUT1}$	All	200	200	200	200	pF max	$DB0-DB11 = V_{DD}$ , $\overline{WR}, \overline{CS} = 0\text{ V}$
<b>DIGITAL INPUTS</b>							
Input High Voltage $V_{IH}$	All	2.4	2.4	13.5	13.5	V min	
Input Low Voltage $V_{IL}$	All	0.8	0.8	1.5	1.5	V max	
Input Current <sup>6</sup> $I_{IN}$	All	$\pm 1$	$\pm 10$	$\pm 1$	$\pm 10$	$\mu\text{A}$ max	$V_{IN} = 0$ or $V_{DD}$
Input Capacitance <sup>3</sup> DB0-DB11	All	5	5	5	5	pF max	$V_{IN} = 0$
$\overline{WR}, \overline{CS}$	All	20	20	20	20	pF max	$V_{IN} = 0$
<b>SWITCHING CHARACTERISTICS<sup>7</sup></b>							
Chip Select to Write Setup Time $t_{CS}$	All	280 200	380 270	180 120	200 150	ns min ns typ	See Timing Diagram
Chip Select to Write Hold Time $t_{CH}$	All	0	0	0	0	ns min	
Write Pulse Width $t_{WR}$	All	250 175	400 280	160 100	240 170	ns min ns typ	$t_{CS} \geq t_{WR}$ , $t_{CH} \geq 0$
Data Setup Time $t_{DS}$	All	140 100	210 150	90 60	120 80	ns min ns typ	
Data Hold Time $t_{DH}$	All	10	10	10	10	ns min	
<b>POWER SUPPLY</b>							
$I_{DD}$	All	2 100 10	2 500 10	2 100 10	2 500 10	mA max $\mu\text{A}$ max $\mu\text{A}$ typ	All Digital Inputs $V_{IL}$ or $V_{IH}$ All Digital Inputs 0 V to $V_{DD}$ All Digital Inputs 0 V to $V_{DD}$

## NOTES

<sup>1</sup>Temperature range as follows: J, K, L, GL versions, 0°C to +70°C; A, B, C, GC versions, -25°C to +85°C; S, T, U GU versions, -55°C to +125°C.

<sup>2</sup>This includes the effect of 5 ppm max gain TC.

<sup>3</sup>Guaranteed but not tested.

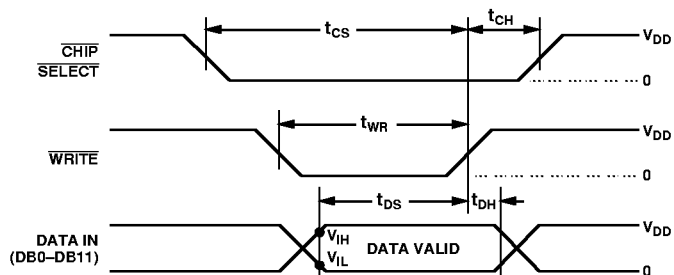
<sup>4</sup> $DB0-DB11 = 0\text{ V}$  to  $V_{DD}$  or  $V_{DD}$  to 0 V.

<sup>5</sup>Feedthrough can be further reduced by connecting the metal lid on the ceramic package (Suffix D) to DGND.

<sup>6</sup>Logic inputs are MOS gates. Typical input current (+25°C) is less than 1 nA.

<sup>7</sup>Sample tested at +25°C to ensure compliance.

Specifications subject to change without notice.



Write Cycle Timing Diagram

MODE SELECTION	
<b>WRITE MODE:</b>	<b>HOLD MODE:</b>
$\overline{CS}$ AND $\overline{WR}$ LOW, DAC RESPONDS TO DATA BUS (DB0-DB11) INPUTS.	EITHER $\overline{CS}$ OR $\overline{WR}$ HIGH, DATA BUS (DB0-DB11) IS LOCKED OUT; DAC HOLDS LAST DATA PRESENT WHEN $\overline{WR}$ OR $\overline{CS}$ ASSUMED HIGH STATE.

NOTES:  
 $V_{DD} = +5V$ ;  $t_r = t_f = 20ns$   
 $V_{DD} = +15V$ ;  $t_r = t_f = 40ns$   
 ALL INPUT SIGNAL RISE AND FALL TIMES MEASURED FROM 10% TO 90% OF  $V_{DD}$   
 TIMING MEASUREMENT REFERENCE LEVEL IS  $V_{IH} + V_{IL}/2$ .

### ABSOLUTE MAXIMUM RATINGS\*

( $T_A = +25^\circ C$  unless otherwise noted)

$V_{DD}$ to DGND	-0.3, +17 V
Digital Input Voltage to DGND	-0.3 V, $V_{DD} + 0.3$ V
$V_{RFB}$ , $V_{REF}$ to DGND	$\pm 25$ V
$V_{PIN1}$ to DGND	-0.3 V, $V_{DD} + 0.3$ V
AGND to DGND	-0.3 V, $V_{DD} + 0.3$ V
Power Dissipation (Any Package) to $+75^\circ C$	450 mW
Derates above $+75^\circ C$	6 mW/ $^\circ C$
Operating Temperature	

Commercial (J, K, L, GL) Grades	$0^\circ C$ to $+70^\circ C$
Industrial (A, B, C, GC) Grades	$-25^\circ C$ to $+85^\circ C$
Extended (S, T, U, GU) Grades	$-55^\circ C$ to $+125^\circ C$
Storage Temperature	$-65^\circ C$ to $+150^\circ C$
Lead Temperature (Soldering, 10 secs)	$+300^\circ C$

\*Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

### CAUTION

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although the AD7545 features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.



### TERMINOLOGY

#### RELATIVE ACCURACY

The amount by which the D/A converter transfer function differs from the ideal transfer function after the zero and full-scale points have been adjusted. This is an endpoint linearity measurement.

#### DIFFERENTIAL NONLINEARITY

The difference between the measured change and the ideal change between any two adjacent codes. If a device has a differential nonlinearity of less than 1 LSB it will be monotonic, i.e., the output will always increase for an increase in digital code applied to the D/A converter.

#### PROPAGATION DELAY

This is a measure of the internal delay of the circuit and is measured from the time a digital input changes to the point at which the analog output at OUT1 reaches 90% of its final value.

#### DIGITAL-TO-ANALOG GLITCH IMPULSE

This is a measure of the amount of charge injected from the digital inputs to the analog outputs when the inputs change state. It is usually specified as the area of the glitch in nV secs and is measured with  $V_{REF} = AGND$  and an ADLH0032CG as the output op amp, C1 (phase compensation) = 33 pF.

### ORDERING GUIDE<sup>1</sup>

Model <sup>2</sup>	Temperature Range	Relative Accuracy	Maximum Gain Error $T_A = +25^\circ C$ $V_{DD} = +5$ V	Package Options <sup>3</sup>
AD7545JN	$0^\circ C$ to $+70^\circ C$	$\pm 2$ LSB	$\pm 20$ LSB	N-20
AD7545AQ	$-25^\circ C$ to $+85^\circ C$	$\pm 2$ LSB	$\pm 20$ LSB	Q-20
AD7545SQ	$-55^\circ C$ to $+125^\circ C$	$\pm 2$ LSB	$\pm 20$ LSB	Q-20
AD7545KN	$0^\circ C$ to $+70^\circ C$	$\pm 1$ LSB	$\pm 10$ LSB	N-20
AD7545BQ	$-25^\circ C$ to $+85^\circ C$	$\pm 1$ LSB	$\pm 10$ LSB	Q-20
AD7545TQ	$-55^\circ C$ to $+125^\circ C$	$\pm 1$ LSB	$\pm 10$ LSB	Q-20
AD7545LN	$0^\circ C$ to $+70^\circ C$	$\pm 1/2$ LSB	$\pm 5$ LSB	N-20
AD7545CQ	$-25^\circ C$ to $+85^\circ C$	$\pm 1/2$ LSB	$\pm 5$ LSB	Q-20
AD7545UQ	$-55^\circ C$ to $+125^\circ C$	$\pm 1/2$ LSB	$\pm 5$ LSB	Q-20
AD7545GLN	$0^\circ C$ to $+70^\circ C$	$\pm 1/2$ LSB	$\pm 1$ LSB	N-20
AD7545GCQ	$-25^\circ C$ to $+85^\circ C$	$\pm 1/2$ LSB	$\pm 1$ LSB	Q-20
AD7545GUQ	$-55^\circ C$ to $+125^\circ C$	$\pm 1/2$ LSB	$\pm 1$ LSB	Q-20
AD7545JP	$0^\circ C$ to $+70^\circ C$	$\pm 2$ LSB	$\pm 20$ LSB	P-20A
AD7545SE	$-55^\circ C$ to $+125^\circ C$	$\pm 2$ LSB	$\pm 20$ LSB	E-20A
AD7545KP	$0^\circ C$ to $+70^\circ C$	$\pm 1$ LSB	$\pm 10$ LSB	P-20A
AD7545TE	$-55^\circ C$ to $+125^\circ C$	$\pm 1$ LSB	$\pm 10$ LSB	E-20A
AD7545LP	$0^\circ C$ to $+70^\circ C$	$\pm 1/2$ LSB	$\pm 5$ LSB	P-20A
AD7545UE	$-55^\circ C$ to $+125^\circ C$	$\pm 1/2$ LSB	$\pm 5$ LSB	E-20A
AD7545GLP	$0^\circ C$ to $+70^\circ C$	$\pm 1/2$ LSB	$\pm 1$ LSB	P-20A
AD7545GUE	$-55^\circ C$ to $+125^\circ C$	$\pm 1/2$ LSB	$\pm 1$ LSB	E-20A

#### NOTES

<sup>1</sup>Analog Devices reserves the right to ship either ceramic (D-20) in lieu of cerdip packages (Q-20).

<sup>2</sup>To order MIL-STD-883, Class B process parts, add /883B to part number. Contact local sales office for military data sheet. For U.S. Standard Military DRAWING (SMD) see DESC drawing 5962-87702.

<sup>3</sup>E = Leadless Ceramic Chip Carrier; N = Plastic DIP; P = Plastic Leaded Chip Carrier; Q = Cerdip.